

Salvatore Lombardo

List of Publications by Year in descending order

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Version: 2024-02-01

16
papers

1,126
citations

933447

10
h-index

1058476

14
g-index

17
all docs

17
docs citations

17
times ranked

1286
citing authors

#	ARTICLE	IF	CITATIONS
1	Dielectric breakdown mechanisms in gate oxides. Journal of Applied Physics, 2005, 98, 121301.	2.5	370
2	Crystal grain nucleation in amorphous silicon. Journal of Applied Physics, 1998, 84, 5383-5414.	2.5	331
3	A Review on Dielectric Breakdown in Thin Dielectrics: Silicon Dioxide, High- κ , and Layered Dielectrics. Advanced Functional Materials, 2020, 30, 1900657.	14.9	119
4	Percolation path and dielectric-breakdown-induced-epitaxy evolution during ultrathin gate dielectric breakdown transient. Applied Physics Letters, 2003, 83, 2223-2225.	3.3	90
5	Dark Current in Silicon Photomultiplier Pixels: Data and Model. IEEE Transactions on Electron Devices, 2012, 59, 2410-2416.	3.0	46
6	Physical mechanism of progressive breakdown in gate oxides. Journal of Applied Physics, 2014, 115, .	2.5	34
7	Breakdown kinetics of Pr ₂ O ₃ films by conductive-atomic force microscopy. Applied Physics Letters, 2005, 87, 231913.	3.3	32
8	Improvement of sensitivity in continuous wave near infrared spectroscopy systems by using silicon photomultipliers. Biomedical Optics Express, 2016, 7, 1183.	2.9	28
9	Characterization of SiPMs With NIR Long-Pass Interferential and Plastic Filters. IEEE Photonics Journal, 2018, 10, 1-12.	2.0	25
10	Characterization of a fiber-less, multichannel optical probe for continuous wave functional near-infrared spectroscopy based on silicon photomultipliers detectors: in-vivo assessment of primary sensorimotor response. Neurophotonics, 2017, 4, 1.	3.3	20
11	Mechanism and kinetics of the ion-assisted nucleation in amorphous silicon. Physical Review B, 1996, 53, 7742-7749.	3.2	10
12	Imaging System Based on Silicon Photomultipliers and Light Emitting Diodes for Functional Near-Infrared Spectroscopy. Applied Sciences (Switzerland), 2020, 10, 1068.	2.5	8
13	Crucial aspects for the use of silicon photomultiplier devices in continuous wave functional near-infrared spectroscopy. Biomedical Optics Express, 2018, 9, 4679.	2.9	7
14	Influence of gate oxides with high thermal conductivity on the failure distribution of InGaAs-based MOS stacks. Microelectronics Reliability, 2016, 56, 22-28.	1.7	6
15	Spatial separation mechanism in Si quantum dots deposited by chemical vapour deposition on SiO ₂ . Materials Research Society Symposia Proceedings, 2003, 788, 1221.	0.1	0
16	Electron Transport and Dielectric Breakdown Kinetics in Pr ₂ O ₃ /High K Films. Advances in Science and Technology, 2006, 46, 21.	0.2	0